

STANDARD RECOVERY DIODES

- **Junction Size:** Rectangular 135 x 100 mils
- **Wafer Size:** 4"
- **V_{RRM} Class:** 1200 V
- **Passivation Process:** Glassivated MOAT
- **Reference IR Packaged Part:** 8EWS..S Series

Major Ratings and Characteristics

Parameters	Units	Test Conditions
V _{FM} Maximum Forward Voltage	1.1 V	T _J = 25°C, I _F = 8 A
V _{RRM} Reverse Breakdown Voltage	1200 V	T _J = 25°C, I _{RRM} = 100 μA (1)

(1) Nitrogen flow on die edge.

Mechanical Characteristics

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 6 KA)
Nominal Front Metal Composition, Thickness	100% Al, (20 μm)
Chip Dimensions	135 x 100 mils (see drawing)
Wafer Diameter	100 mm, with std. < 110 > flat
Wafer Thickness	300 μm, ± 10 μm
Maximum Width of Sawing Line	45 μm
Reject Ink Dot Size	0.25 mm diameter minimum
Ink Dot Location	See drawing
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

IR135DM12CCB

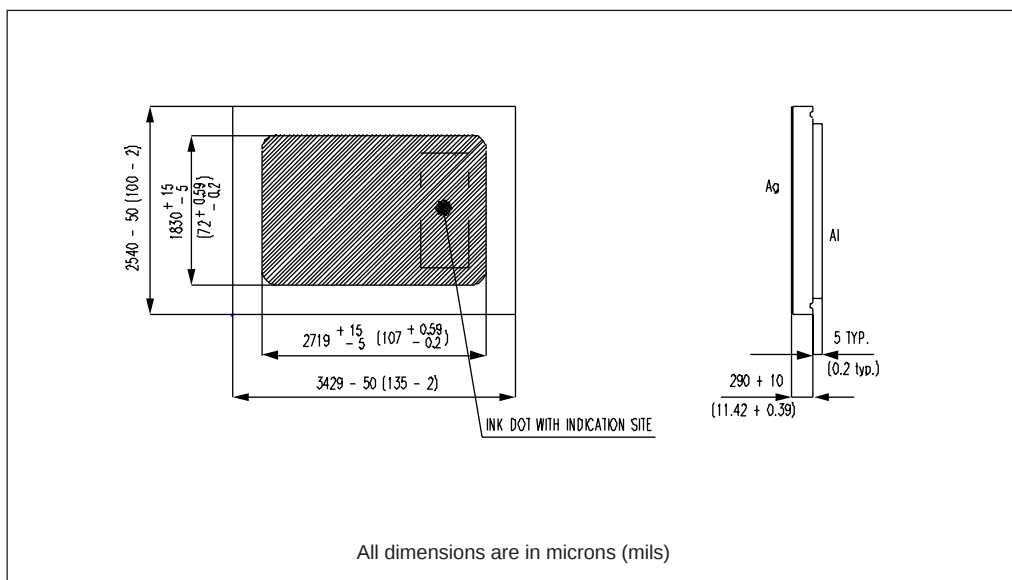
Bulletin I0122J rev. A 02/97

International
IR Rectifier

Ordering Information Table

Device Code						
IR	135	D	M	12	C	CB
①	②	③	④	⑤	⑥	⑦
1	- International Rectifier Device					
2	- Chip Dimension in Mils					
3	- Type of Device: D = Wire Bondable Standard Recovery Diode					
4	- Passivation Process: M = Glassivated MOAT					
5	- Voltage code: Code x 100 = V_{RRM}					
6	- Metallization: C = Aluminium (Anode) - Silver (Cathode)					
7	- CB = Probed Uncut Die (wafer in box) None = Probed Die in chip carrier					

Outline Table



Wafer Layout

